# MSKSEMI















**ESD** 

TVS

TSS

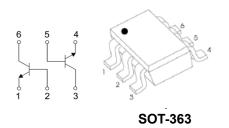
MOV

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# Broduct data sheet





#### **DUAL TRANSISTOR (NPN+NPN)**

#### **FEATURES**

- Two transistors in one package
- Reduces number of components and board space
- No mutual interference between the transistors

**MARKING: 4Ft** 

# MAXIMUM RATINGS( $T_a$ =25°C unless otherwise noted)

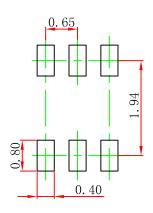
Symbol	Parameter	Value	Units	
V <sub>CBO</sub>	Collector-Base Voltage	80	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	65	V	
V <sub>EBO</sub>	Emitter-Base Voltage	6	V	
Ic	Collector Current –Continuous	0.1	Α	
Pc	Collector Dissipation	200	mW	
TJ	Junction Temperature	150	℃	
T <sub>stg</sub>	Storage Temperature	-55-150	$^{\circ}$	

#### **ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)**

Parameter Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =10μA,I <sub>E</sub> =0	80			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =10mA,I <sub>B</sub> =0	65			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =10μA,I <sub>C</sub> =0	6			V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =30V,I <sub>E</sub> =0			15	nA
Emitter cut-off current	I <sub>EBO</sub>	I <sub>C</sub> =0, V <sub>EB</sub> =5V			5	μA
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> =5V,I <sub>C</sub> =2mA	110		600	
Collector-emitter saturation voltage	V <sub>CE(sat)(1)</sub>	I <sub>C</sub> =10mA,I <sub>B</sub> =0.5mA			0.1	V
Conector-entitler Saturation voltage	V <sub>CE(sat)(2)</sub>	I <sub>C</sub> =100mA,I <sub>B</sub> =5mA			0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I <sub>C</sub> =10mA,I <sub>B</sub> =0.5mA		0.77		V
Transition frequency	f⊤	V <sub>CB</sub> =5V,I <sub>E</sub> =10mA,f=100MHz	100			MHz
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> =10V,I <sub>E</sub> =0,f=1MHz			1.5	pF

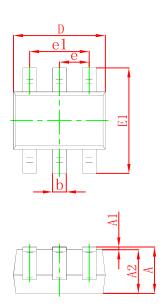


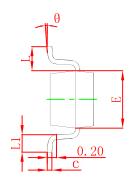
SOT-363



#### Note:

- 1.Controlling dimension:in millimeters.2.General tolerance:± 0.05mm.3.The pad layout is for reference purposes only.





Symbol	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	0.900	1.100	0.035	0.043	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.000	0.035	0.039	
b	0.150	0.350	0.006	0.014	
С	0.100	0.150	0.004	0.006	
D	2.000	2.200	0.079	0.087	
E	1.150	1.350	0.045	0.053	
E1	2.150	2.400	0.085	0.094	
е	0.650	) TYP	0.026	S TYP	
e1	1.200	1.400	0.047	0.055	
L	0.525 REF		0.021 REF		
L1	0.260	0.460	0.010	0.018	
θ	0°	8°	0°	8°	

# **REEL SPECIFICATION**

P/N	PKG	QTY
BC846S	SOT-363	3000



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